

**TO-220-2L Plastic-Encapsulate Diode****MUR8H120**

HYPERFAST RECTIFIER,FRED

MAIN CHARACTERISTICS

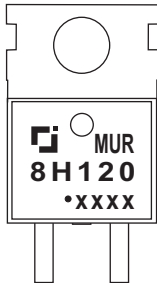
I_o	8A
V_{RRM}	1200V
T_{rr}	23.5ns
T_j	175°C
V_{F(typ)}	1.7V(@T_j=150°C)

FEATURES

- Ultrafast Recovery Times and Low Recovery Loss
- Low Forward Voltage
- Low Reverse Leakage Current

APPLICATIONS

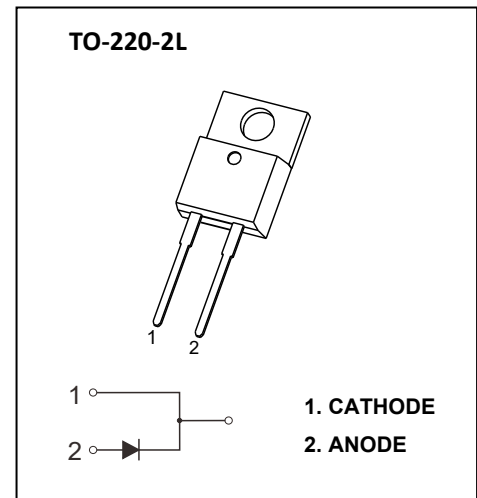
Specifically designed to improve efficiency of PFC and output rectification stages of EV / HEV battery charging stations, booster stage of solar inverters and UPS applications, these devices are perfectly matched to operate with MOSFETs or high speed IGBTs.

MARKING

MUR8H120 = Device code

Solid dot = Green molding compound device
if none, the normal device

XXXX = Code

**MAXIMUM RATINGS (T_c=25°C unless otherwise noted)**

Symbol	Parameter	MUR8H120	Unit
V_{RRM}	Peak Repetitive Reverse Voltage	1200	V
V_R	DC Blocking Voltage		
I_{F(AV)}	Average Forward Current(T _c =146°C)	8	A
I_{F(RMS)}	RMS Forward Current(T _c =146°C)	11	A
I_{FSM}	Non-Repetitive Surge Forward Current (8.3ms)	100	A
P_D	Power dissipation	75	W
R_{θJC}	Thermal Resistance From Junction to Case	2.0	°C/W
T_j	Operating Junction Temperature Range	-55 ~ +175	°C
T_{stg}	Storage Temperature Range	-55 ~ +175	°C

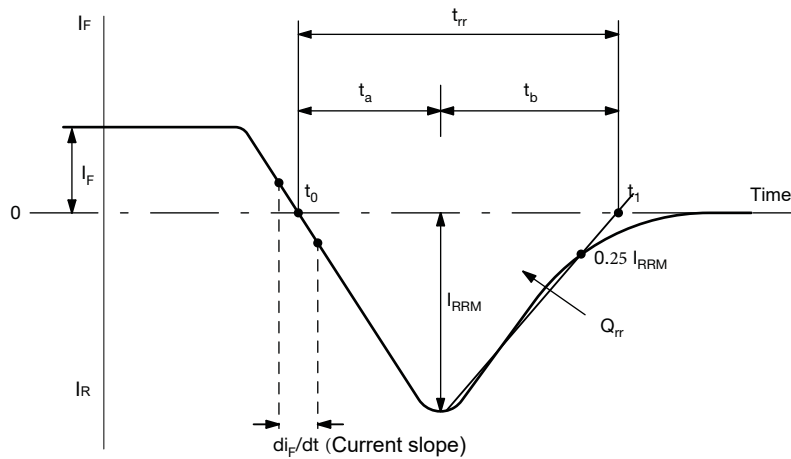
Typical Characteristics

ELECTRICAL CHARACTERISTICS ($T_c=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)}$	Reverse Voltage	$I_R=100\mu\text{A}$	1200			V
I_R	Reverse Current	$V_R=1200\text{V}$	$T_J=25^\circ\text{C}$		10	μA
			$T_J=150^\circ\text{C}$		500	μA
V_F	Forward Voltage	$I_F=8\text{A}$	$T_J=25^\circ\text{C}$	2.4	3.0	V
			$T_J=150^\circ\text{C}$	1.7		V
C_{tot}	Total Capacitance	$V_R=200\text{V}, f=1\text{MHz}$		6		pF
t_{rr}	Reverse Recovery time	$I_F=0.5\text{A}, I_R=1\text{A}, I_{rr}=0.25\text{A}$		28		ns
		$I_F=1\text{A}, V_R=30\text{V}, di_F/dt = 200\text{A/us}$		23.5		ns

ELECTRICAL CHARACTERISTICS ($T_c=25^\circ\text{C}$ unless otherwise specified)

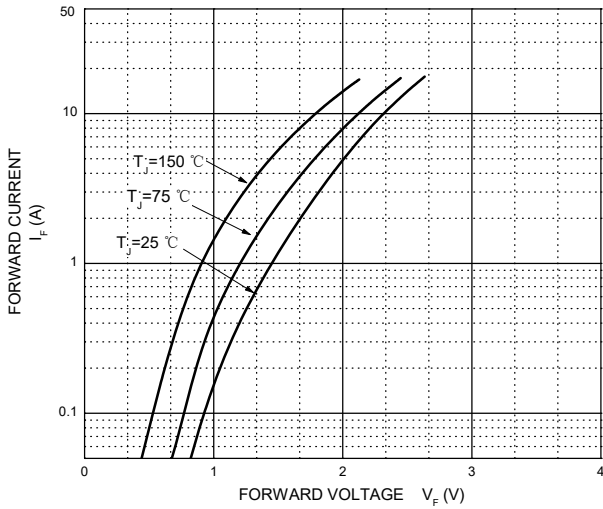
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
t_{rr}	Reverse Recovery Time	$I_F=8\text{A}, V_R=600\text{V}, di_F/dt=200\text{A}/\mu\text{s}$		61		ns
I_{RRM}	Max. Reverse Recovery Current			4.8		A
Q_{rr}	Reverse Recovery Charge			166		nC
t_{rr}	Reverse Recovery Time	$I_F=8\text{A}, V_R=600\text{V}, di_F/dt=200\text{A}/\mu\text{s}, T_J=125^\circ\text{C}$		115		ns
I_{RRM}	Max. Reverse Recovery Current			8.3		A
Q_{rr}	Reverse Recovery Charge			559		nC
t_{rr}	Reverse Recovery Time	$I_F=8\text{A}, V_R=600\text{V}, di_F/dt=500\text{A}/\mu\text{s}, T_J=125^\circ\text{C}$		67		ns
I_{RRM}	Max. Reverse Recovery Current			14.5		A
Q_{rr}	Reverse Recovery Charge			555		nC



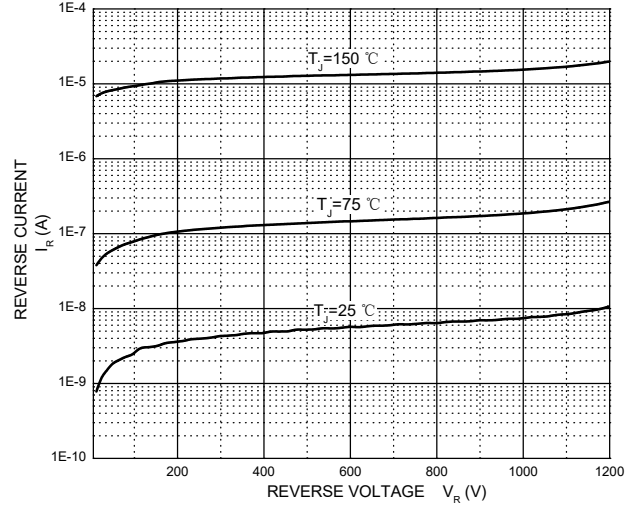
Reverse Recovery Waveform and Definitions

Typical Characteristics

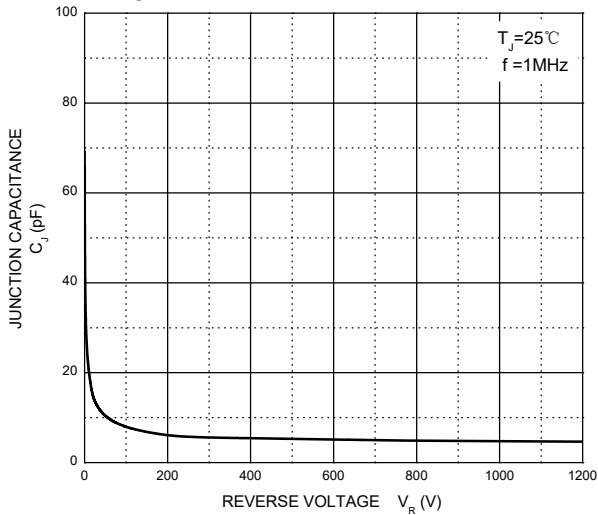
Forward Characteristics



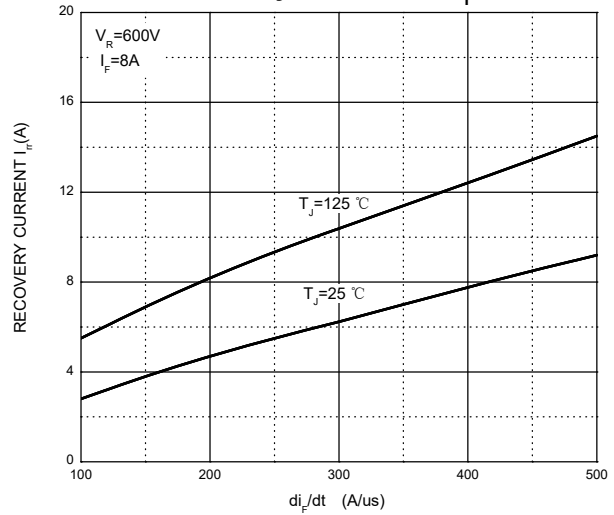
Reverse Characteristics



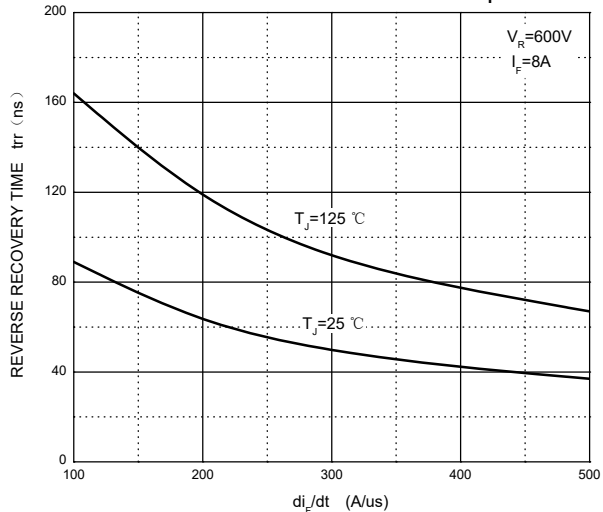
Capacitance Characteristics Per Diode



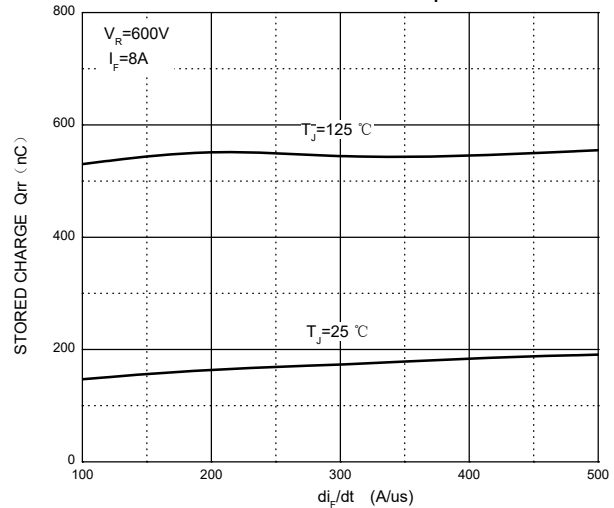
Recovery Current vs. di_F/dt



Reverse Recovery Time vs. di_F/dt

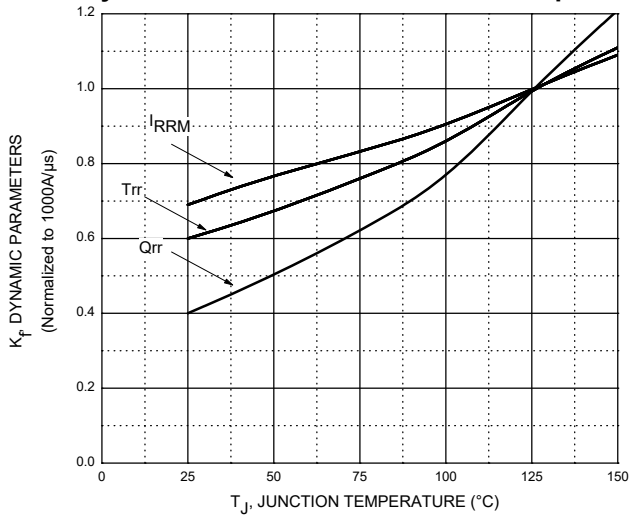


Stored Charge vs. di_F/dt

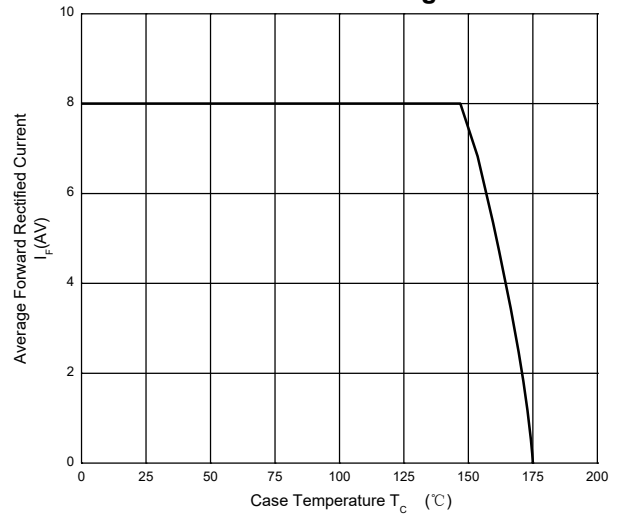


Typical Characteristics

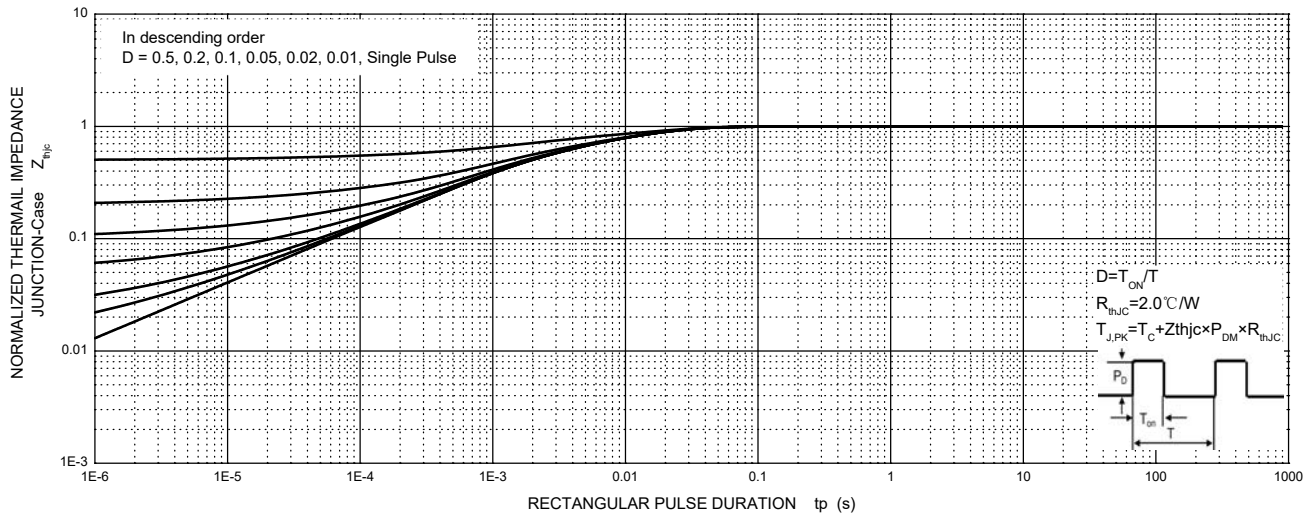
Dynamic Parameters vs. Junction Temperature



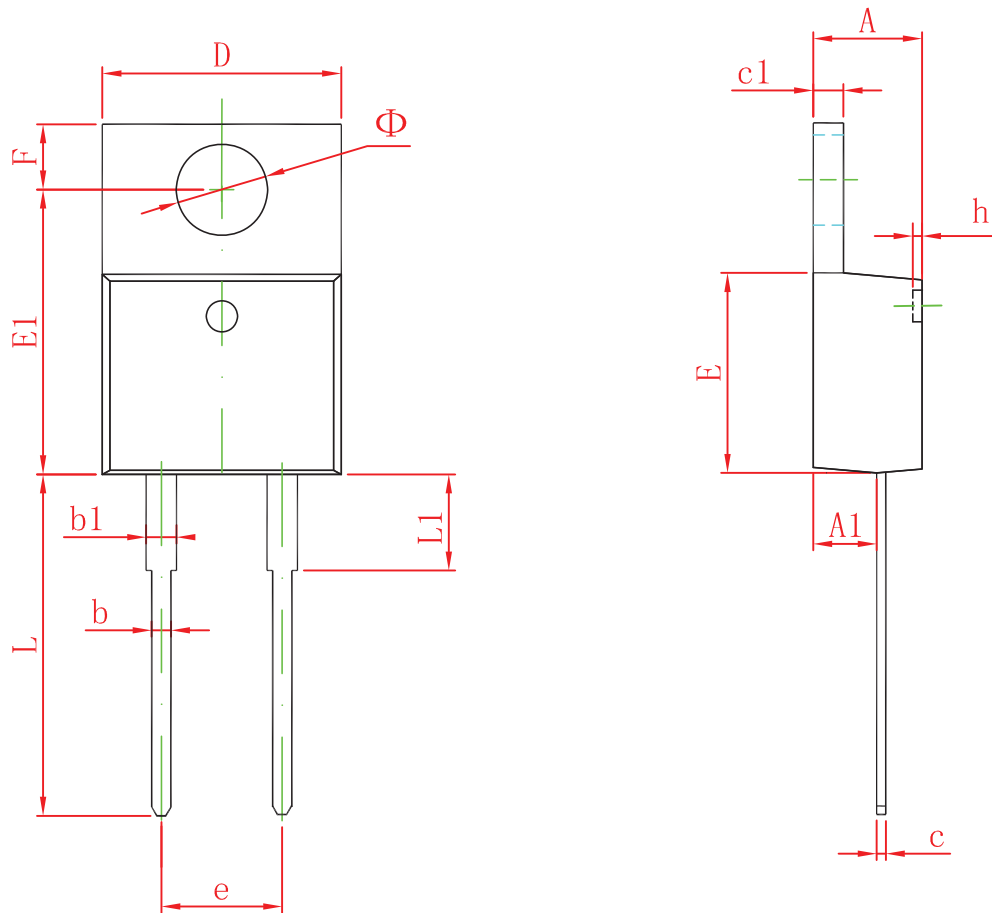
Current Derating



MUR8H120 Transient Thermal Impedance, Junction-Case



TO-220-2L Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	4.450	4.750	0.175	0.187
A1	2.520	2.820	0.099	0.111
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.300	0.500	0.012	0.020
c1	1.170	1.370	0.046	0.054
D	9.830	10.330	0.387	0.407
E	8.500	8.900	0.335	0.350
E1	12.050	12.650	0.474	0.498
e	5.080 TYP		0.200 TYP	
F	2.540	2.940	0.100	0.116
h	0.100 TYP		0.004 TYP	
L	13.300	13.800	0.523	0.543
L1	3.540	3.940	0.139	0.155
Φ	3.735	3.935	0.147	0.155